

30V_{DS}/±20V_{GS} N-Channel Enhancement Mode MOSFET

Description

The IP15N03M has the characteristics of extremely low $R_{DS(ON)}$, high-speed switching and high efficiency in DC/DC conversion, marking it suitable for load switching and DC/DC converters.

Application

- Load Switch
- DC/DC conversion
- Portable and Battery-powered Products

General Features

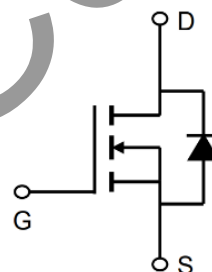
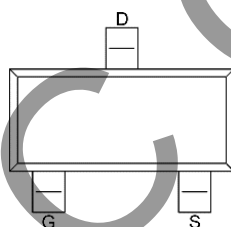
- $V_{DS}=30V, I_D=8A$
- $R_{DS(ON)}=14.5m\Omega$ (TYP.) $V_{GS}=10V, I_D=5A$
- $R_{DS(ON)}=17m\Omega$ (TYP.) $V_{GS}=4.5V, I_D=4A$
- Reliable and Rugged
- Avalanche Rated
- Low On-Resistance

Bottom view



SOT-23L

Top view



schematic diagram

Package Marking and Ordering Information

Product ID	Pack		Marking	Qty(PCS)
IP15N03M	SOT23-3L	Pb-Free	IP15N03M	3000pcs/Reel

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Absolute Maximum Ratings ($T_C=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Value	Units
V_{DS}	Drain-Source Voltage ($V_{GS}=0\text{V}$)	30	V
V_{GS}	Gate-Source Voltage ($V_{GS}=0\text{V}, \text{static}$)	± 20	V
I_D	Continuous Drain Current ($T_C=25^{\circ}\text{C}$)	8	A
	Continuous Drain Current ($T_C=100^{\circ}\text{C}$)	6	A
I_{DM}	Pulsed Drain Current	32	A
E_{AS}	Single Pulsed Avalanche Energy	42	mJ
P_D	Maximum Power Dissipation ($T_C=25^{\circ}\text{C}$)	1.3	W
	Maximum Power Dissipation ($T_C=100^{\circ}\text{C}$)	0.7	W
T_J, T_{STG}	Operating, Storage Temperature Range	$-55 \sim 150$	$^{\circ}\text{C}$

Thermal Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JL}$	Thermal Resistance, Junction-to-Lead	-	61	-	$^{\circ}\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	-	88	-	$^{\circ}\text{C}/\text{W}$

Electrical Characteristics ($T_C=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=30\text{V}, V_{GS}=0\text{V}$	-	-	1	μA
I_{GSS}	Gate -Source Leakage Current	$V_{GS}=\pm 20\text{V}, V_{DS}=0\text{V}$	-	-	± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1.1	1.5	1.9	V
$R_{DS(on)}$	Drain-Source On-stage Resistance	$V_{GS}=10\text{V}, I_D=5\text{A}$	-	14.5	18.5	m Ω
		$V_{GS}=4.5\text{V}, I_D=4\text{A}$	-	17	22	

Dynamic Characteristics

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
C_{iss}	Input capacitance	$V_{DS}=15V$ $V_{GS}=0V$ $f=1MHz$	-	745	-	pF
C_{oss}	Output capacitance		-	80	-	
C_{rss}	Reverse transfer capacitance		-	70	-	
R_g	Gate Resistance	$f=1MHz$	-	3.1	-	Ω
Q_g	Total Gate Charge	$V_{DS}=15V$ $V_{GS}=10V$ $I_D=6A$	-	14.6	-	nC
Q_{gs}	Gate Source Charge		-	2.3	-	
Q_{gd}	Gate Drain Charge		-	3.1	-	
$t_{d(on)}$	Turn-on delay Time	$V_{GS}=10V$ $V_{DS}=15V$ $I_D=6A$ $R_G=1.8\Omega$	-	8	-	ns
t_r	Rise time		-	95	-	
$t_{d(off)}$	Turn-off delay Time		-	26	-	
t_f	Fall time		-	72	-	

Reverse Diode Characteristics

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
V_{SD}	Body Diode Forward Voltage	$V_{GS}=0V, I_{SD}=1A$	-	0.8	1	V
t_{rr}	Reverse Recovery Time	$V_{GS}=0V, I_{SD}=6A$ $di/dt=100A/\mu s$	-	15	-	ns
Q_{rr}	Reverse Recovery Charge		-	26	-	nC

Notes :

- (1) The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper
- (2) The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- (3) The power dissipation is limited by 150°C junction temperature
- (4) The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation

Typical Characteristics

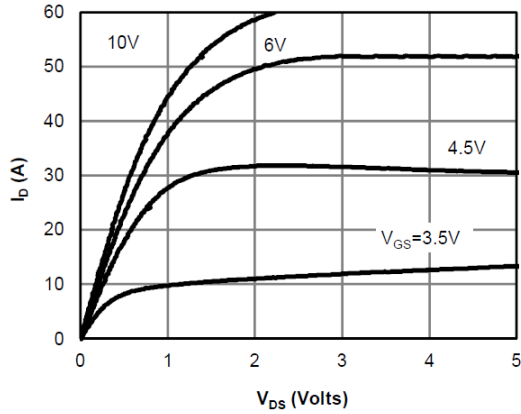


Figure 1. On-Region Characteristics

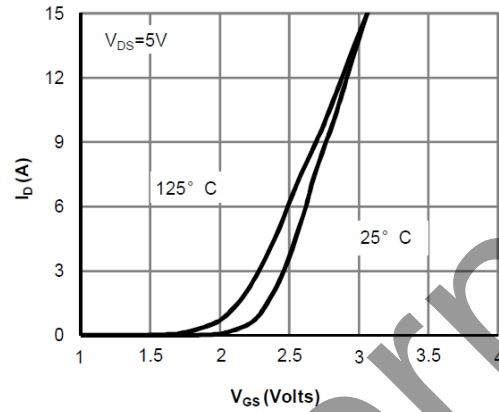


Figure 2. Transfer Characteristics

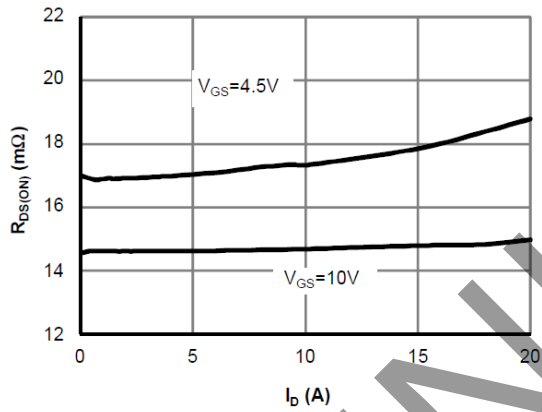


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

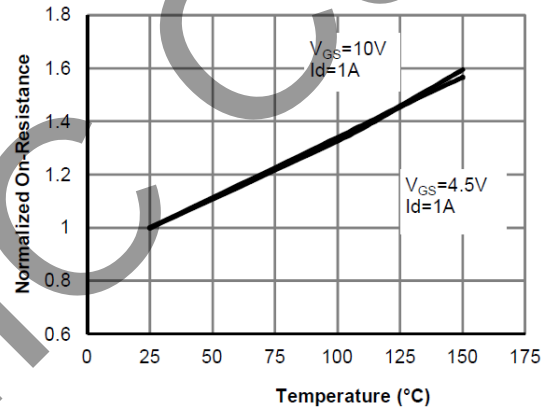


Figure 4. On-Resistance vs. Junction Temperature

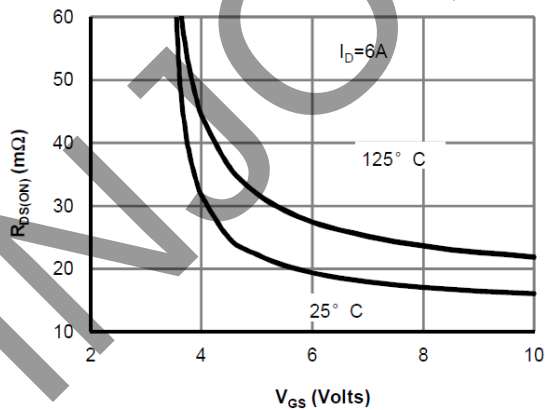


Figure 5. On-Resistance vs. Gate-Source Voltage

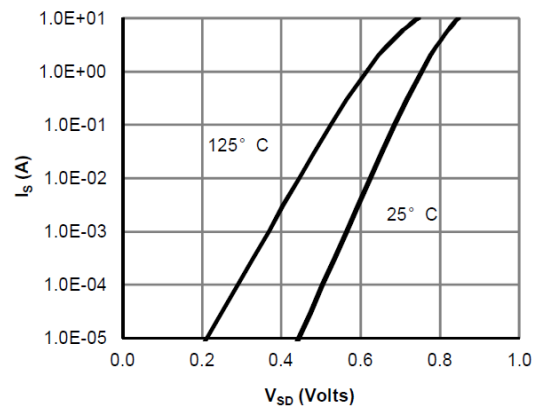


Figure 6. Body-Diode Characteristics

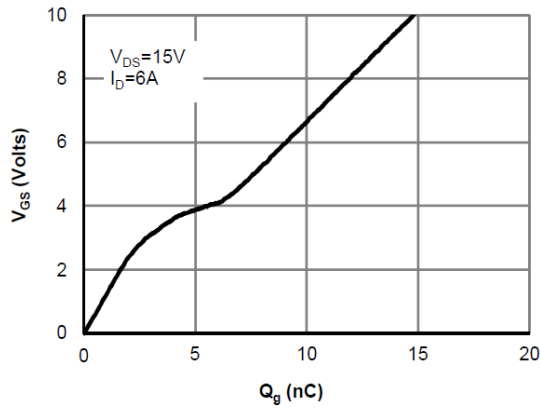


Figure 7. Gate-Charge Characteristics

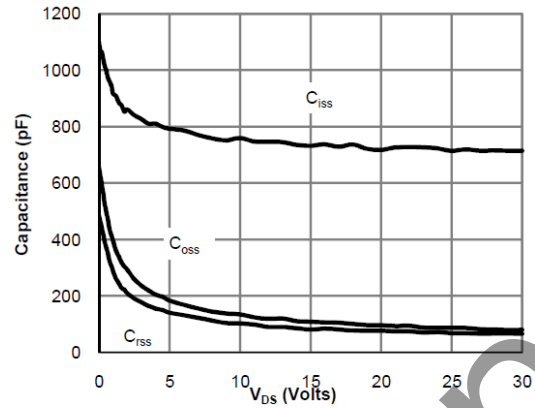


Figure 8. Capacitance Characteristics

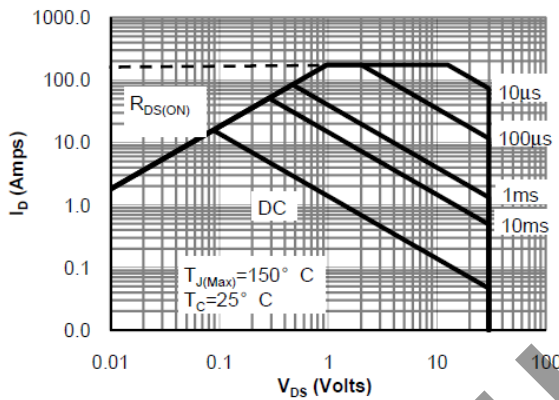


Figure 9. Maximum Forward Biased Safe Operating Area

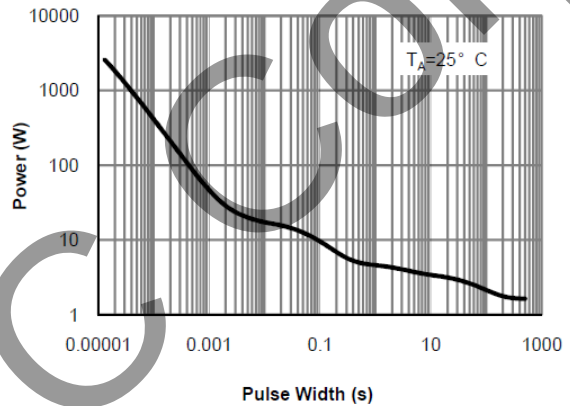


Figure 10. Single Pulse Power Rating Junction-to-Ambient

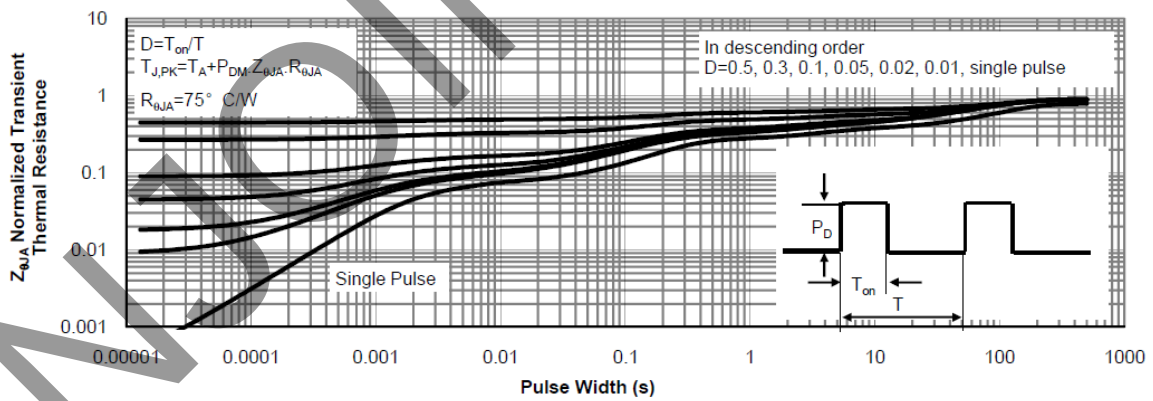
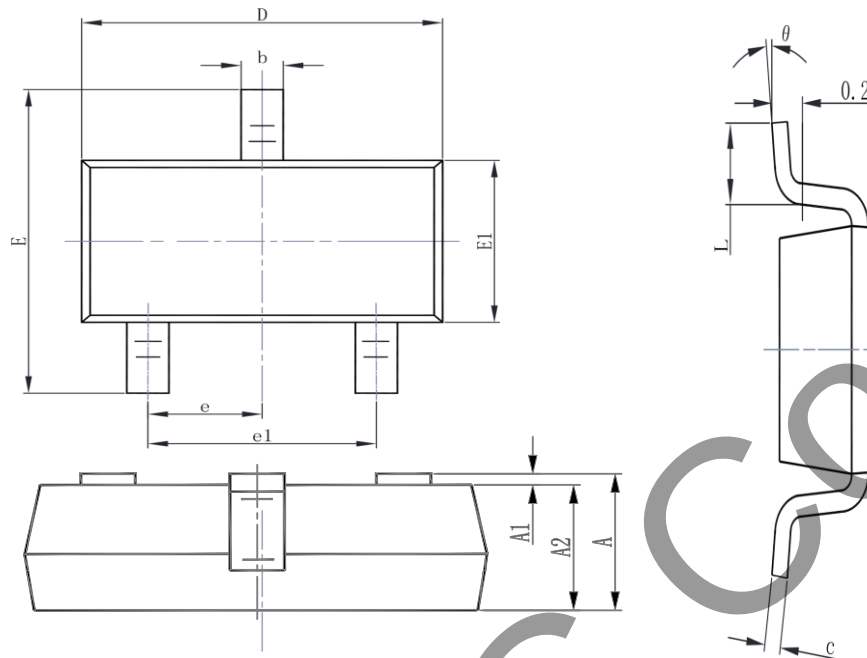


Figure 11. Normalized Maximum Transient Thermal Impedance

Package Mechanical Data-SOT23-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

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